



Vishay Siliconix

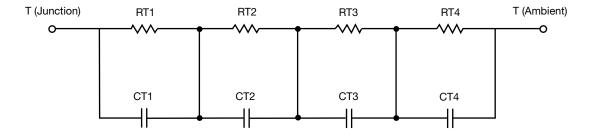
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	CONFIGURATION		
	THERMAL RES	SISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	N/A	241.4165m	N/A
RT2	N/A	305.3967m	N/A
RT3	N/A	2.9292	N/A
RT4	N/A	523.9868m	N/A
·	THERMAL CAPAC	ITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	N/A	2.7875m	N/A
CT2	N/A	75.3129m	N/A
CT3	N/A	447.5456m	N/A
CT4	N/A	5.6503m	N/A

Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

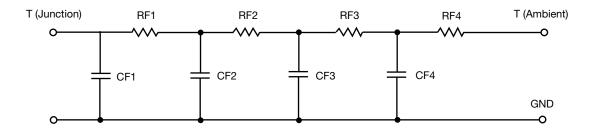
1





Vishay Siliconix

R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	778.3955m	N/A		
RF2	N/A	421.0045m	N/A		
RF3	N/A	1.5741	N/A		
RF4	N/A	1.2265	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	2.1988m	N/A		
CF2	N/A	56.1516m	N/A		
CF3	N/A	369.8909m	N/A		
CF4	N/A	243.6504m	N/A		

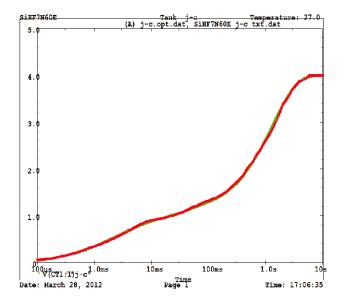
Note

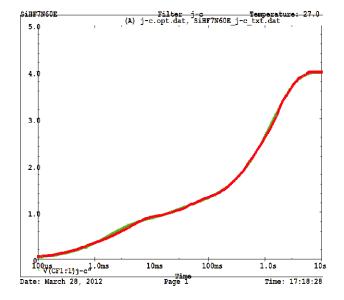
• n/a indicates not applicable



SiHF7N60E_RC

Vishay Siliconix





Revision: 04-Apr-12